

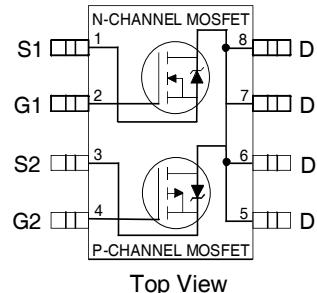
## Features

N-Ch:

- $V_{DS} (V) = 30V$
- $R_{DS(ON)} < 29m\Omega$  ( $V_{GS} = 10V$ )
- $R_{DS(ON)} < 46 m\Omega$  ( $V_{GS} = 4.5V$ )

P-Ch:

- $V_{DS} (V) = -30V$
- $R_{DS(ON)} < 58m\Omega$  ( $V_{GS} = -10V$ )
- $R_{DS(ON)} < 98 m\Omega$  ( $V_{GS} = -4.5V$ )
- Generation V Technology
- Ultra Low On-Resistance
- Complimentary Half Bridge
- Surface Mount
- Fully Avalanche Rated
- Lead-Free



Top View

## Description

The SOP-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infrared, or wave soldering techniques.

## Absolute Maximum Ratings ( $T_A = 25^\circ C$ Unless Otherwise Noted)

	Symbol	Maximum		Units
		N-Channel	P-Channel	
Drain-Source Voltage	$V_{DS}$	30	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current <sup>⑤</sup>	$I_D$	7.3	-5.3	A
		5.9	-4.2	
Pulsed Drain Current	$I_{DM}$	30	-30	
Continuous Source Current (Diode Conduction)	$I_S$	2.5	-2.5	
Maximum Power Dissipation <sup>⑤</sup>	$P_D$	2.5		W
		1.6		
Single Pulse Avalanche Energy	$E_{AS}$	82	140	mJ
Avalanche Current	$I_{AR}$	4.0	-2.8	A
Repetitive Avalanche Energy	$E_{AR}$	0.20		mJ
Peak Diode Recovery dv/dt <sup>②</sup>	$dv/dt$	3.8	-2.2	V/ns
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to + 150 °C		

## Thermal Resistance Ratings

Parameter	Symbol	Limit	Units
Maximum Junction-to-Ambient <sup>③</sup>	$R_{JJA}$	50	°C/W

### Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter		Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{DSS}}$	Drain-to-Source Breakdown Voltage	N-Ch	30			V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
		P-Ch	-30				$V_{GS} = 0V, I_D = -250\mu\text{A}$
$\Delta V_{(\text{BR})\text{DSS}}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	N-Ch	0.022			V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
		P-Ch	0.022				Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
$R_{DS(\text{ON})}$	Static Drain-to-Source On-Resistance		23	29		$\text{m}\Omega$	$V_{GS} = 10V, I_D = 5.8\text{A}$ ④
		N-Ch	32	46			$V_{GS} = 4.5V, I_D = 4.7\text{A}$ ④
			42	58			$V_{GS} = -10V, I_D = -4.9\text{A}$ ④
		P-Ch	76	98			$V_{GS} = -4.5V, I_D = -3.6\text{A}$ ④
$V_{GS(\text{th})}$	Gate Threshold Voltage	N-Ch	1.0			V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
		P-Ch	-1.0				$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
$g_{fs}$	Forward Transconductance	N-Ch	—	14	—	S	$V_{DS} = 15V, I_D = 5.8\text{A}$ ④
		P-Ch	—	7.7	—		$V_{DS} = -15V, I_D = -4.9\text{A}$ ④
$I_{DSS}$	Drain-to-Source Leakage Current	N-Ch	—	—	1.0	$\mu\text{A}$	$V_{DS} = 24V, V_{GS} = 0V$ ④
		P-Ch	—	—	-1.0		$V_{DS} = -24V, V_{GS} = 0V$
		N-Ch	—	—	25		$V_{DS} = 24V, V_{GS} = 0V, T_J = 55^\circ\text{C}$
		P-Ch	—	—	-25		$V_{DS} = -24V, V_{GS} = 0V, T_J = 55^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	N-P	—	—	$\pm 100$		$V_{GS} = \pm 20V$
$Q_g$	Total Gate Charge	N-Ch	—	22	33	nC	N-Channel
		P-Ch	—	23	34		$I_D = 5.8\text{A}, V_{DS} = 15V, V_{GS} = 10V$ ④
$Q_{gs}$	Gate-to-Source Charge	—	—	—	—		P-Channel
		—	—	—	—		$I_D = -4.9\text{A}, V_{DS} = -15V, V_{GS} = -10V$
$t_{d(on)}$	Turn-On Delay Time	N-Ch	—	8.1	12	ns	N-Channel
		P-Ch	—	13	19		$V_{DD} = 15V, I_D = 1.0\text{A}, R_G = 6.0\Omega, R_D = 15\Omega$ ④
$t_r$	Rise Time	N-Ch	—	8.9	13		
		P-Ch	—	13	20		
$t_{d(off)}$	Turn-Off Delay Time	N-Ch	—	26	39	ns	P-Channel
		P-Ch	—	34	51		$V_{DD} = -15V, I_D = -1.0\text{A}, R_G = 6.0\Omega, R_D = 15\Omega$
$t_f$	Fall Time	N-Ch	—	17	26		
		P-Ch	—	32	48		
$C_{iss}$	Input Capacitance	N-Ch	—	650	—	pF	N-Channel
		P-Ch	—	710	—		$V_{GS} = 0V, V_{DS} = 25V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	N-Ch	—	320	—		P-Channel
		P-Ch	—	380	—		$V_{GS} = 0V, V_{DS} = -25V, f = 1.0\text{MHz}$
$C_{rss}$	Reverse Transfer Capacitance	N-Ch	—	130	—		
		P-Ch	—	180	—		

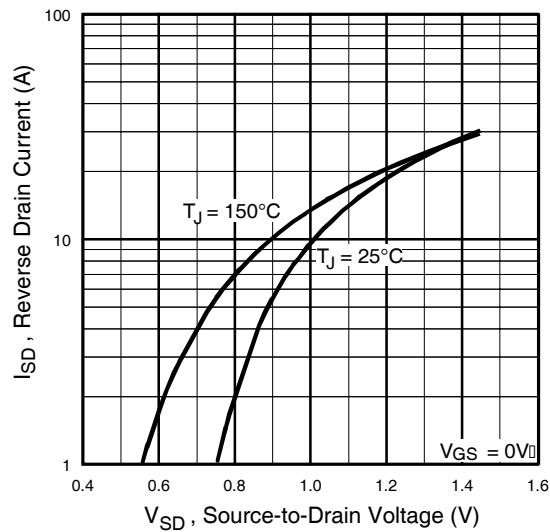
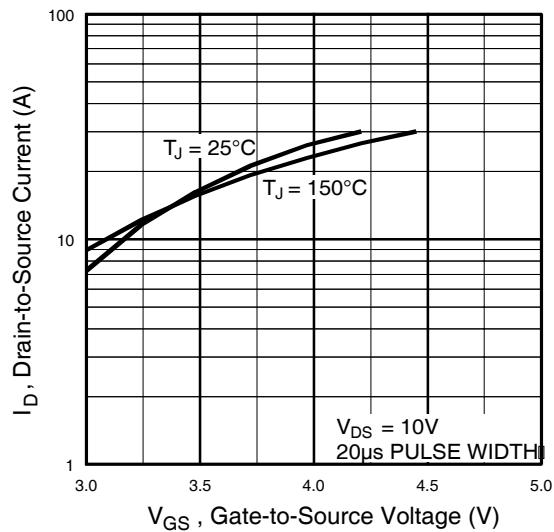
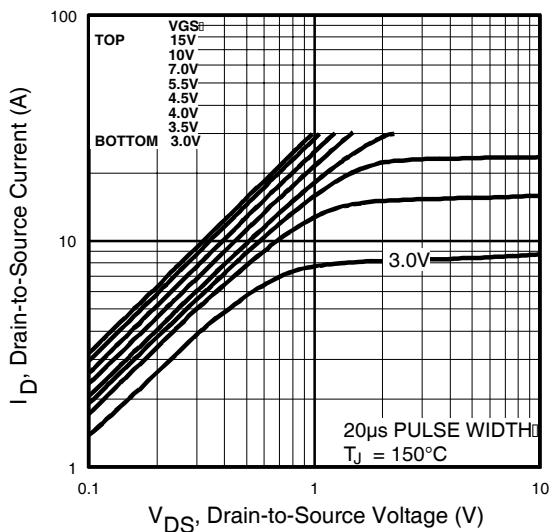
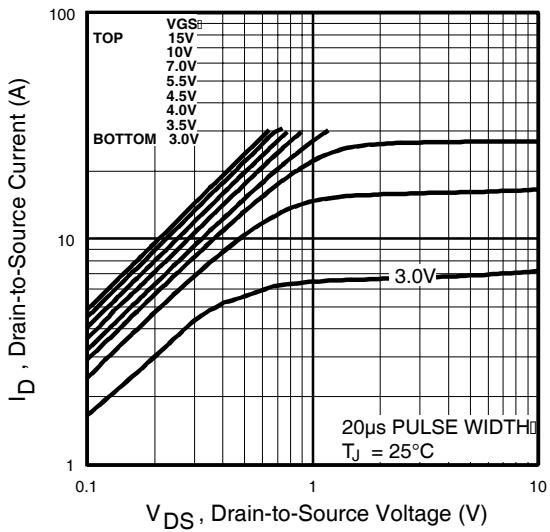
### Source-Drain Ratings and Characteristics

	Parameter		Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	N-Ch	—	—	2.5	A	
		P-Ch	—	—	-2.5		
$I_{SM}$	Pulsed Source Current (Body Diode) ④	N-Ch	—	—	30	A	
		P-Ch	—	—	-30		
$V_{SD}$	Diode Forward Voltage	N-Ch	—	0.78	1.0	V	$T_J = 25^\circ\text{C}, I_S = 1.7\text{A}, V_{GS} = 0V$ ③
		P-Ch	—	-0.78	-1.0		$T_J = 25^\circ\text{C}, I_S = -1.7\text{A}, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	N-Ch	—	45	68	ns	N-Channel
		P-Ch	—	44	66		$T_J = 25^\circ\text{C}, I_F = 1.7\text{A}, di/dt = 100\text{A}/\mu\text{s}$
$Q_{rr}$	Reverse Recovery Charge	N-Ch	—	58	87	nC	P-Channel
		P-Ch	—	42	63		$T_J = 25^\circ\text{C}, I_F = -1.7\text{A}, di/dt = 100\text{A}/\mu\text{s}$ ④

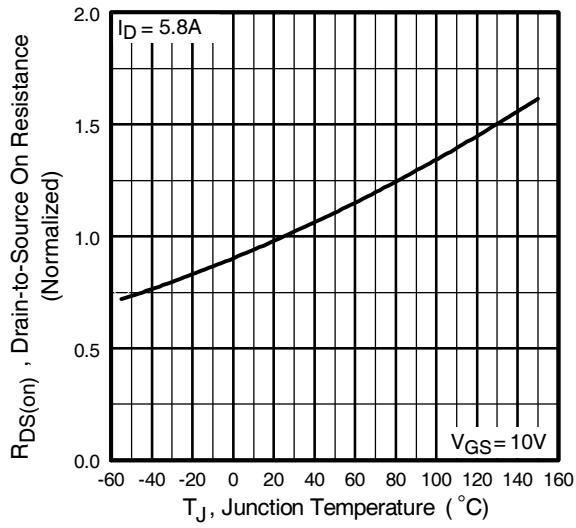
#### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 22 )
- ② N-Channel  $I_{SD} \leq 4.0\text{A}$ ,  $di/dt \leq 74\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(\text{BR})\text{DSS}}$ ,  $T_J \leq 150^\circ\text{C}$   
P-Channel  $I_{SD} \leq -2.8\text{A}$ ,  $di/dt \leq 150\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(\text{BR})\text{DSS}}$ ,  $T_J \leq 150^\circ\text{C}$
- ③ N-Channel Starting  $T_J = 25^\circ\text{C}$ ,  $L = 10\text{mH}$   $R_G = 25\Omega$ ,  $I_{AS} = 4.0\text{A}$ . (See Figure 12)  
P-Channel Starting  $T_J = 25^\circ\text{C}$ ,  $L = 35\text{mH}$   $R_G = 25\Omega$ ,  $I_{AS} = -2.8\text{A}$ .
- ④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤ Surface mounted on FR-4 board,  $t \leq 10\text{sec}$ .

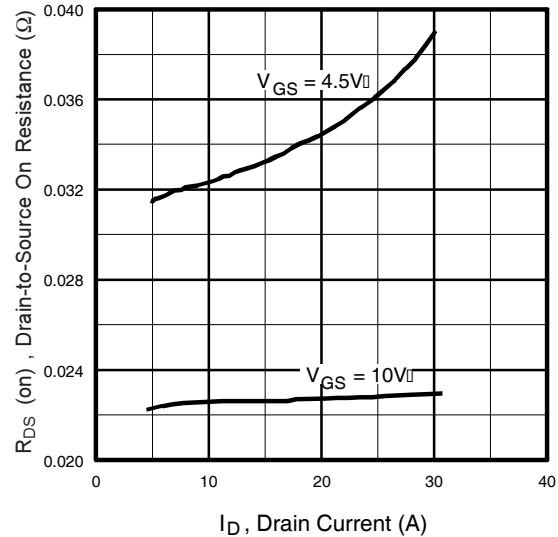
N-Channel



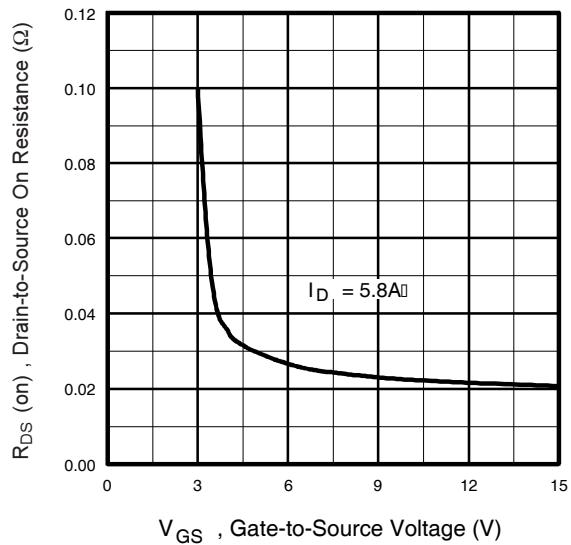
### N-Channel



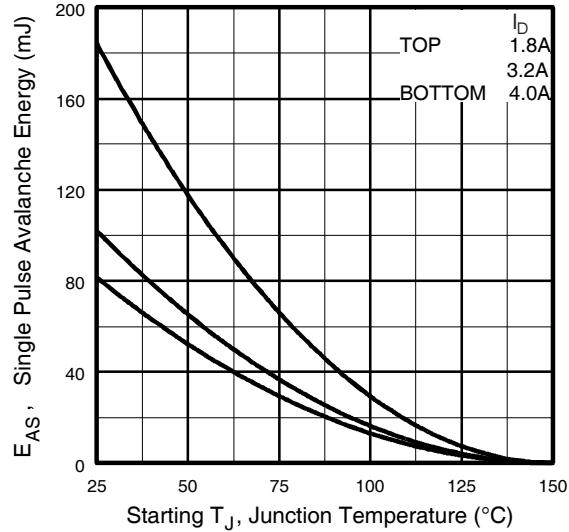
**Fig 5.** Normalized On-Resistance Vs. Temperature



**Fig 6.** Typical On-Resistance Vs. Drain Current

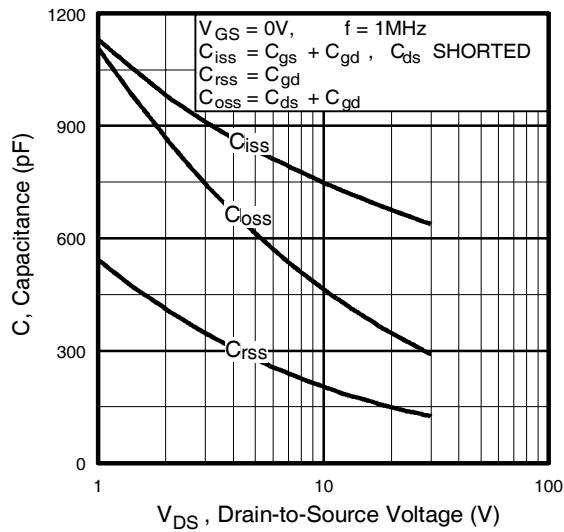


**Fig 7.** Typical On-Resistance Vs. Gate Voltage

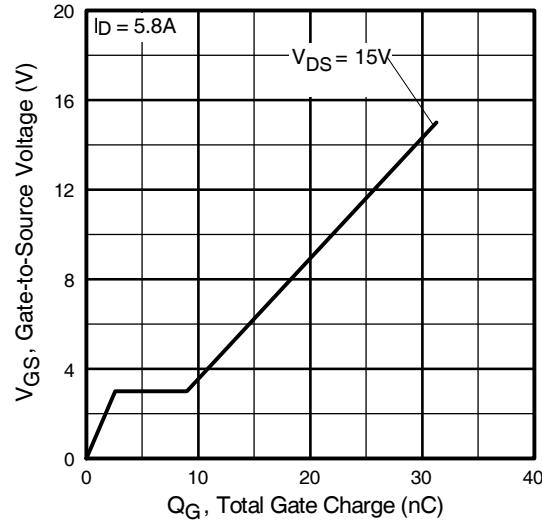


**Fig 8.** Maximum Avalanche Energy Vs. Drain Current

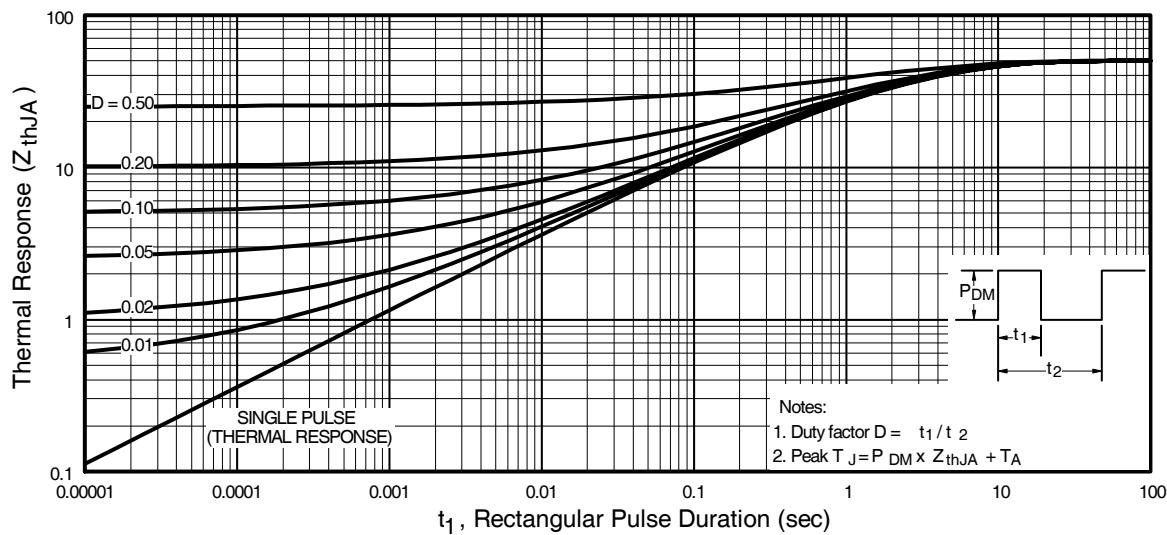
### N-Channel



**Fig 9.** Typical Capacitance Vs.  
Drain-to-Source Voltage

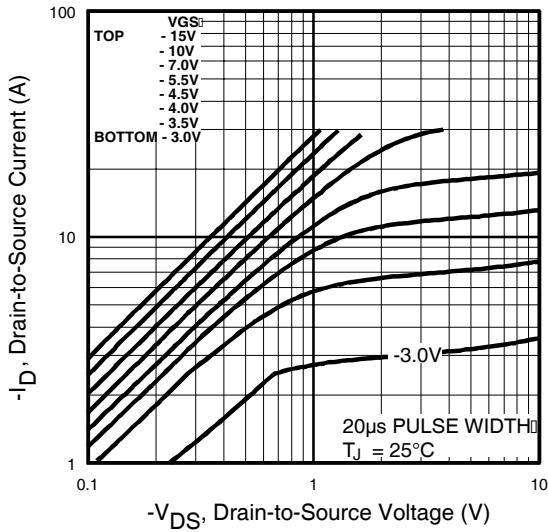


**Fig 10.** Typical Gate Charge Vs.  
Gate-to-Source Voltage

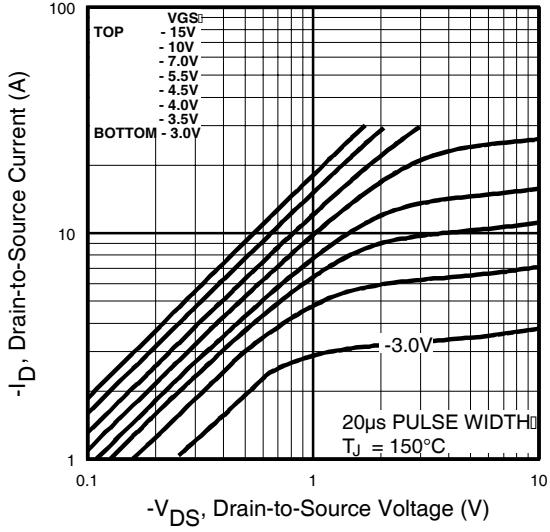


**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

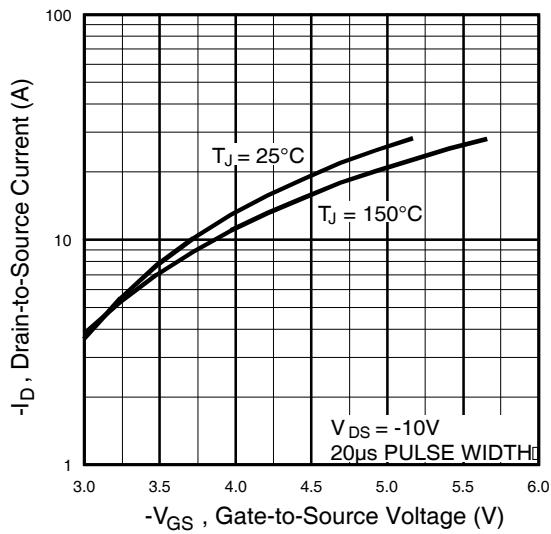
P-Channel



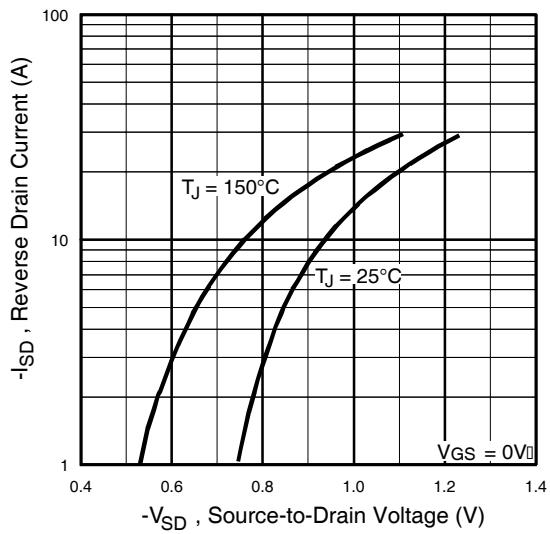
**Fig 12.** Typical Output Characteristics



**Fig 13.** Typical Output Characteristics

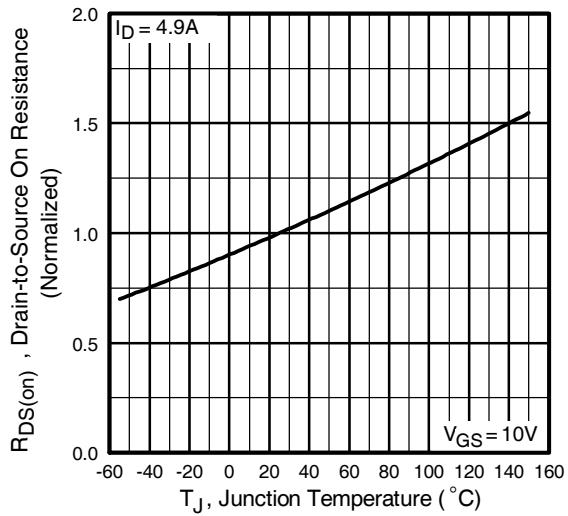


**Fig 14.** Typical Transfer Characteristics

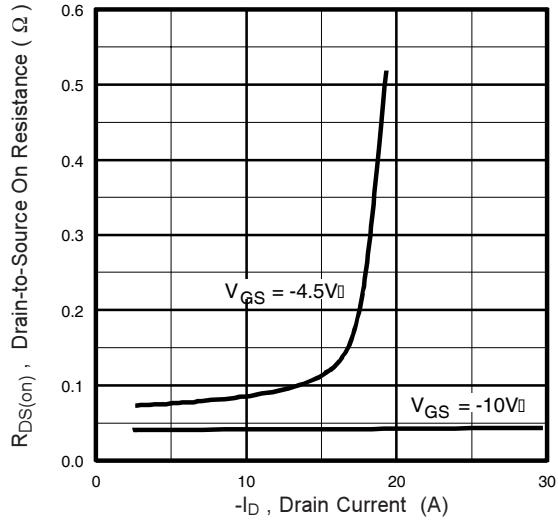


**Fig 15.** Typical Source-Drain Diode Forward Voltage

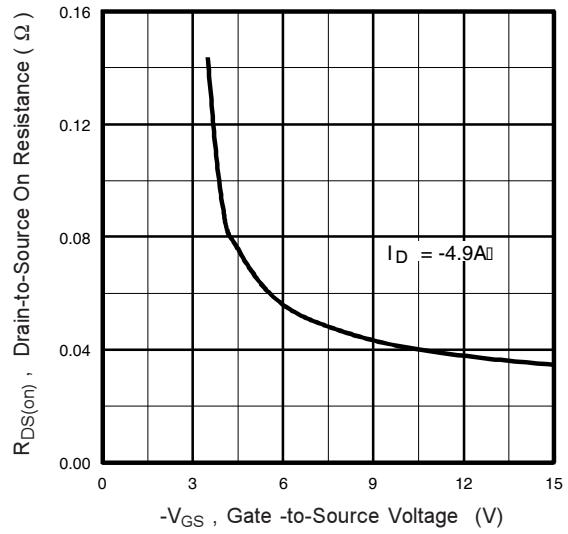
P-Channel



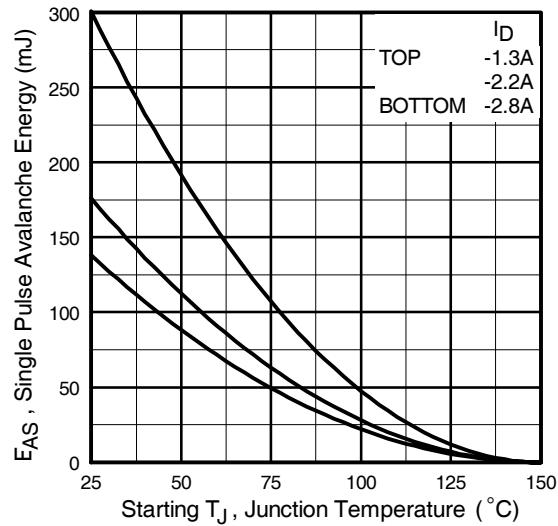
**Fig 16.** Normalized On-Resistance Vs. Temperature



**Fig 17.** Typical On-Resistance Vs. Drain Current

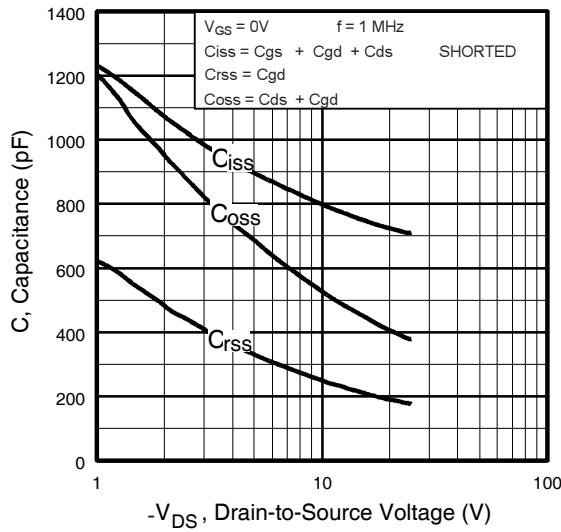


**Fig 18.** Typical On-Resistance Vs. Gate Voltage

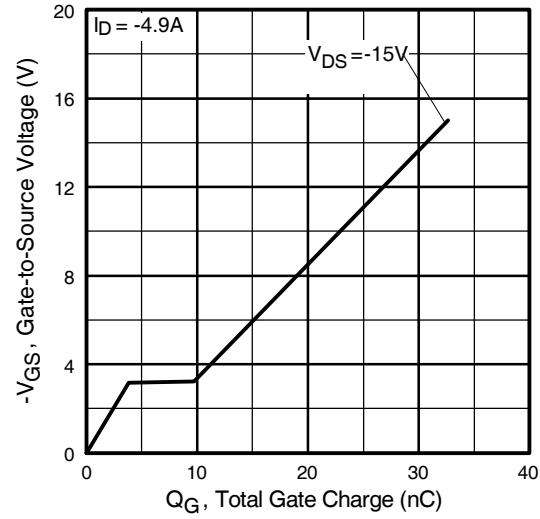


**Fig 19.** Maximum Avalanche Energy Vs. Drain Current

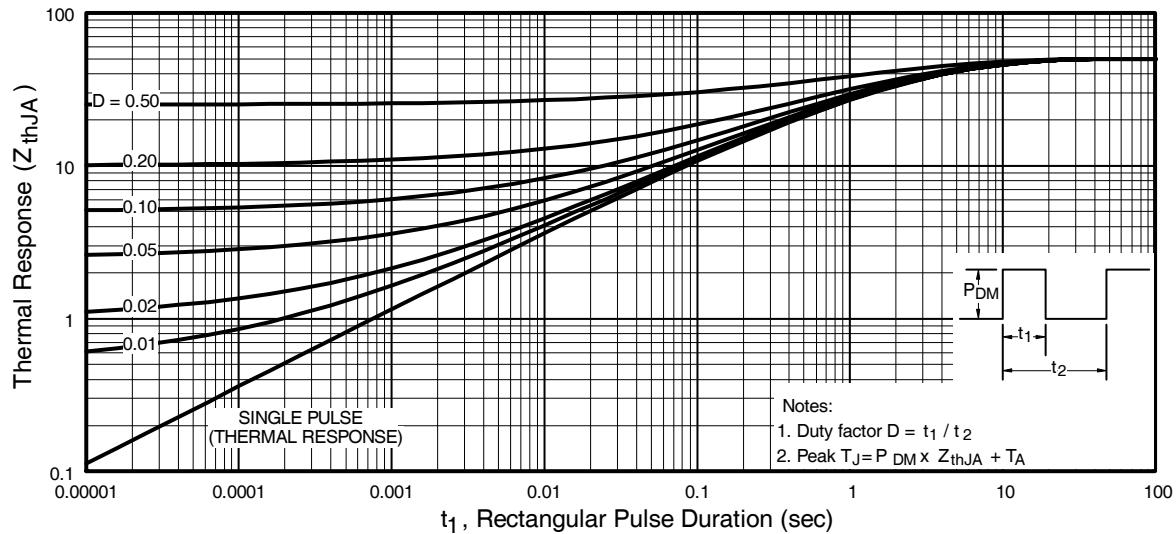
P-Channel



**Fig 20.** Typical Capacitance Vs.  
Drain-to-Source Voltage

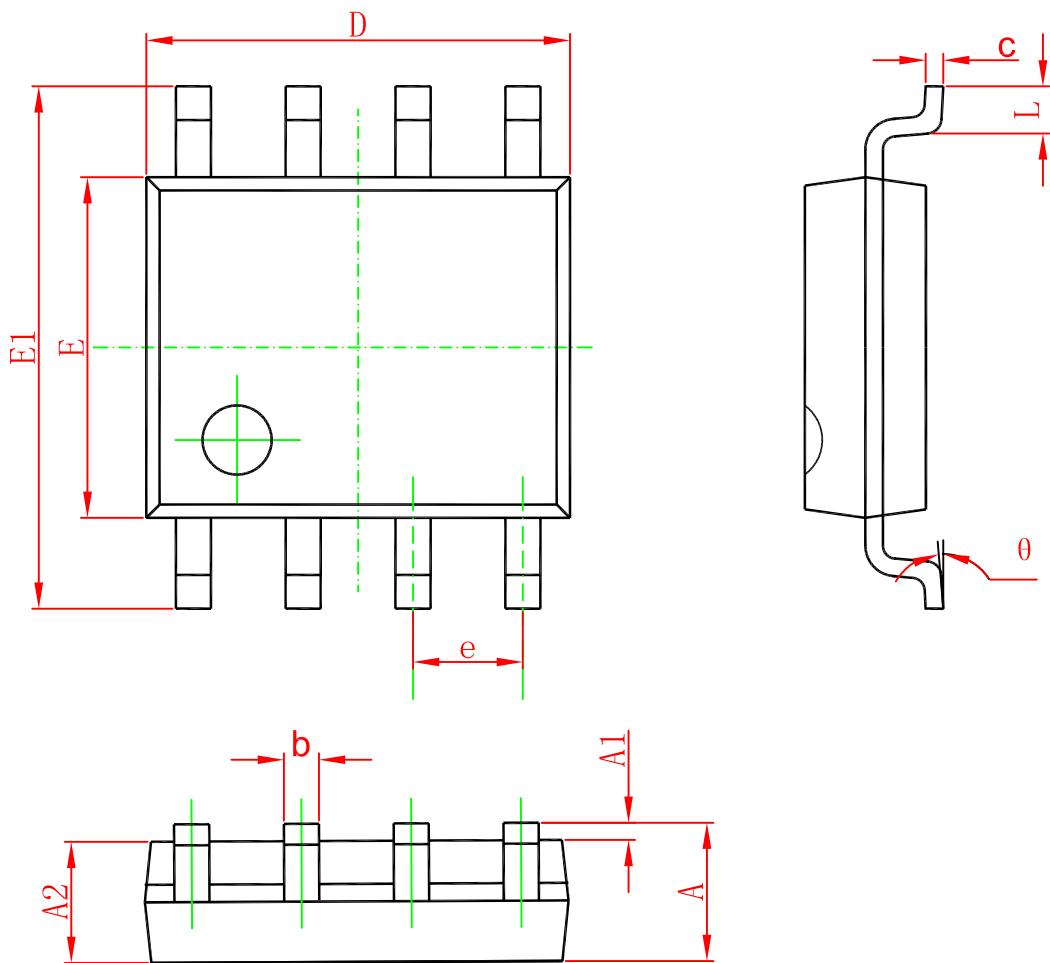


**Fig 21.** Typical Gate Charge Vs.  
Gate-to-Source Voltage



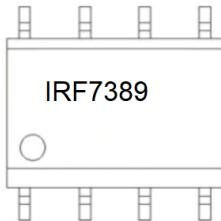
**Fig 22.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

**SOP-8**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

## Marking



## Ordering information

Order code	Package	Baseqty	Deliverymode
IRF7389TR	SOP-8	3000	Tape and reel